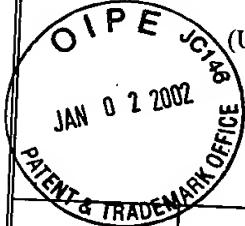


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LIST OF DOCUMENTS CITED BY APPLICANT				Applicants: Ryu, et al.			
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FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
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<table border="1"> <tr> <td rowspan="2">O I P E JAN 02 2002 P A T E N T & T R A D E M A R K S O C I E T Y 1999</td> <td>V. R. Vathulya, H. Shang, and M. H. White, "A Novel 6H-SiC Power DMOSFET with Implanted P-Well Spacer." <i>IEEE Electron Device Letters</i>, Vol. 20, No. 7, July 1999, pp. 354-356. ✓</td> </tr> <tr> <td>30 A.K. Agarwal, S. Seshadri, and L. B. Rowland, "Temperature Dependence of Fowler-Nordheim Current in 6H-and 4H-SiC MOS Capacitors." <i>IEEE Electron Device Letters</i>, Vol. 18, No. 12, Dec. 1997, pp. 592-594. ✓</td> </tr> <tr> <td>31 P. J. Tobin, Y. Okada, S. A. Ajuria, V. Lakhota, W. A. Feil, and R. I. Hedge, "Furnace formation of silicon oxynitride thin dielectrics in nitrous oxide (N₂O): The role of nitric oxide (NO)." <i>Journal of Applied Physics</i>, Vol. 75, No. 3, February 1, 1994, pp. 1811-1817. ✓</td> </tr> <tr> <td>32 Sze, S.M. <i>Physics of Semiconductor Devices</i>, John Wiley & Sons, p. 383-390, (1981). ✓</td> </tr> <tr> <td>33 H.F. Li, S. Dimitrijev, H.B. Harrison, D. Sweatman, and P.T. Tanner. "Improving SiO₂ Grown on P-Type 4H-SiC by NO Annealing." <i>Materials Science Forum</i>, Vols. 264-268 (1998) pp. 869-872. ✓</td> </tr> <tr> <td>34 K. Ueno, R. Asai, and T. Tsuji. "4H-SiC MOSFET's Utilizing the H₂ Surface Cleaning Technique." <i>IEEE Electron Device Letters</i>, Vol. 19, No. 7, July 1998, pp. 244-246. ✓</td> </tr> <tr> <td>35 Chung et al. "The Effect of Si:C Source Ratio on SiO₂/SiC Interface State Density for Nitrogen Doped 4H and 6H-SiC." <i>Materials Science Forum</i>, (2000) Vols. 338-342, pp. 1097-1100. ✓</td> </tr> <tr> <td>36 Pantelides et al. "Atomic-Scale Engineering of the SiC-SiO₂ Interface," <i>Materials Science Forum</i>, (2000) Vols. 338-342, pp. 1133-1136. ✓</td> </tr> <tr> <td>37 Das, Mrinal K. Graduate thesis entitled, <i>Fundamental Studies of the Silicon Carbide MOS Structure</i>. Purdue University. No publication data ✓</td> </tr> </table>				O I P E JAN 02 2002 P A T E N T & T R A D E M A R K S O C I E T Y 1999	V. R. Vathulya, H. Shang, and M. H. White, "A Novel 6H-SiC Power DMOSFET with Implanted P-Well Spacer." <i>IEEE Electron Device Letters</i> , Vol. 20, No. 7, July 1999, pp. 354-356. ✓	30 A.K. Agarwal, S. Seshadri, and L. B. Rowland, "Temperature Dependence of Fowler-Nordheim Current in 6H-and 4H-SiC MOS Capacitors." <i>IEEE Electron Device Letters</i> , Vol. 18, No. 12, Dec. 1997, pp. 592-594. ✓	31 P. J. Tobin, Y. Okada, S. A. Ajuria, V. Lakhota, W. A. Feil, and R. I. Hedge, "Furnace formation of silicon oxynitride thin dielectrics in nitrous oxide (N ₂ O): The role of nitric oxide (NO)." <i>Journal of Applied Physics</i> , Vol. 75, No. 3, February 1, 1994, pp. 1811-1817. ✓	32 Sze, S.M. <i>Physics of Semiconductor Devices</i> , John Wiley & Sons, p. 383-390, (1981). ✓	33 H.F. Li, S. Dimitrijev, H.B. Harrison, D. Sweatman, and P.T. Tanner. "Improving SiO ₂ Grown on P-Type 4H-SiC by NO Annealing." <i>Materials Science Forum</i> , Vols. 264-268 (1998) pp. 869-872. ✓	34 K. Ueno, R. Asai, and T. Tsuji. "4H-SiC MOSFET's Utilizing the H ₂ Surface Cleaning Technique." <i>IEEE Electron Device Letters</i> , Vol. 19, No. 7, July 1998, pp. 244-246. ✓	35 Chung et al. "The Effect of Si:C Source Ratio on SiO ₂ /SiC Interface State Density for Nitrogen Doped 4H and 6H-SiC." <i>Materials Science Forum</i> , (2000) Vols. 338-342, pp. 1097-1100. ✓	36 Pantelides et al. "Atomic-Scale Engineering of the SiC-SiO ₂ Interface," <i>Materials Science Forum</i> , (2000) Vols. 338-342, pp. 1133-1136. ✓	37 Das, Mrinal K. Graduate thesis entitled, <i>Fundamental Studies of the Silicon Carbide MOS Structure</i> . Purdue University. No publication data ✓
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Applicants: Ryu, et al.

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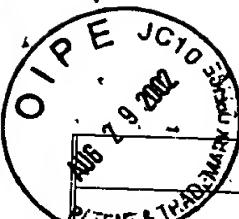
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